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EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		European Supplementary Search Report, with Written Opinion, issued in European Patent Application No. EP 04773759.8/1672683 dated on September 2, 2008
		ITO et al "10-15nm Ultrashallow Junction Formation by Flash-Lamp Annealing" pages 2394-2398 Japanese Journal of Applied Physics, Tokyo, Japan Vol. 41, No. 4b September 26, 2001

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